

FIG. 1

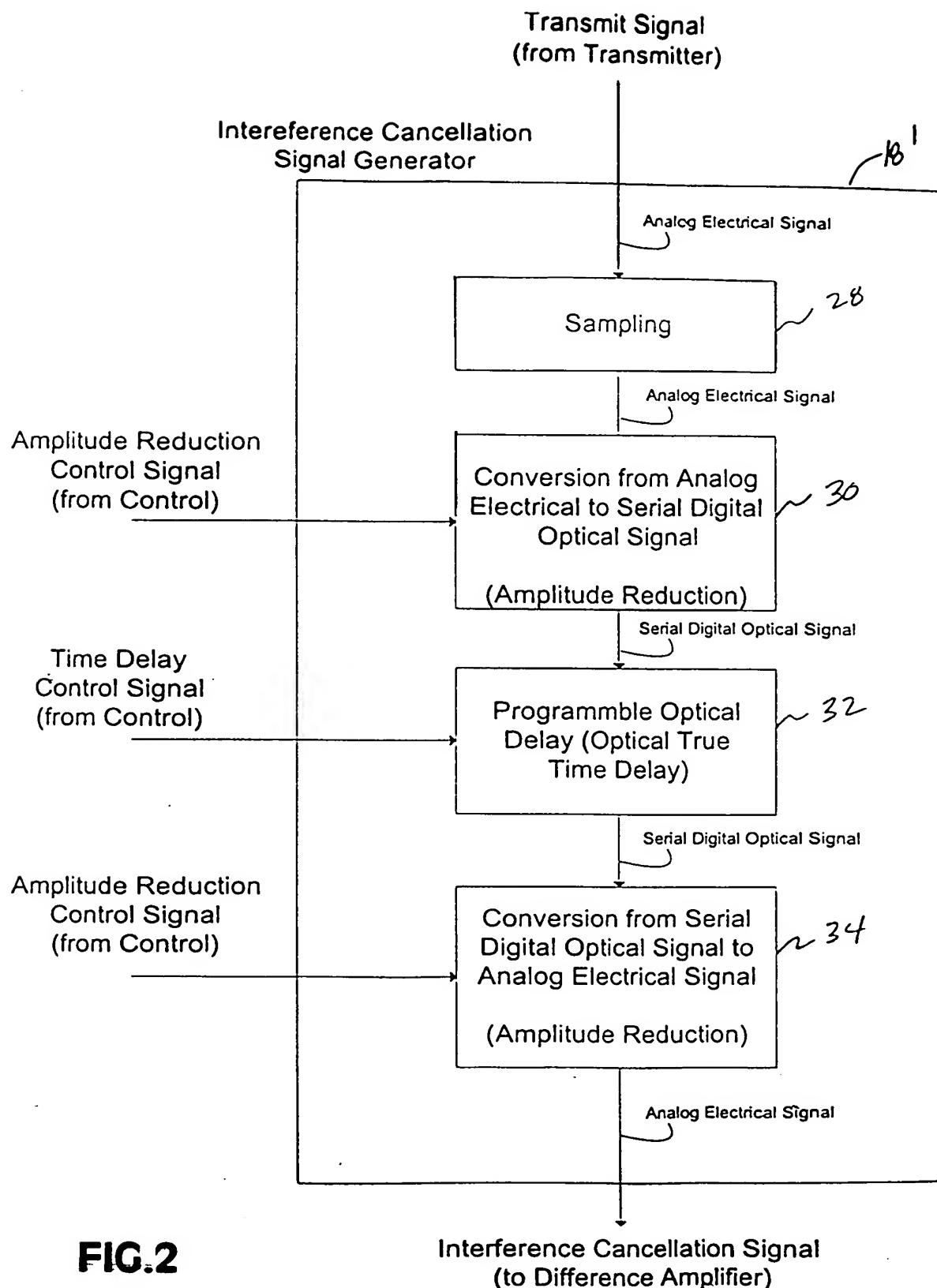


FIG.2

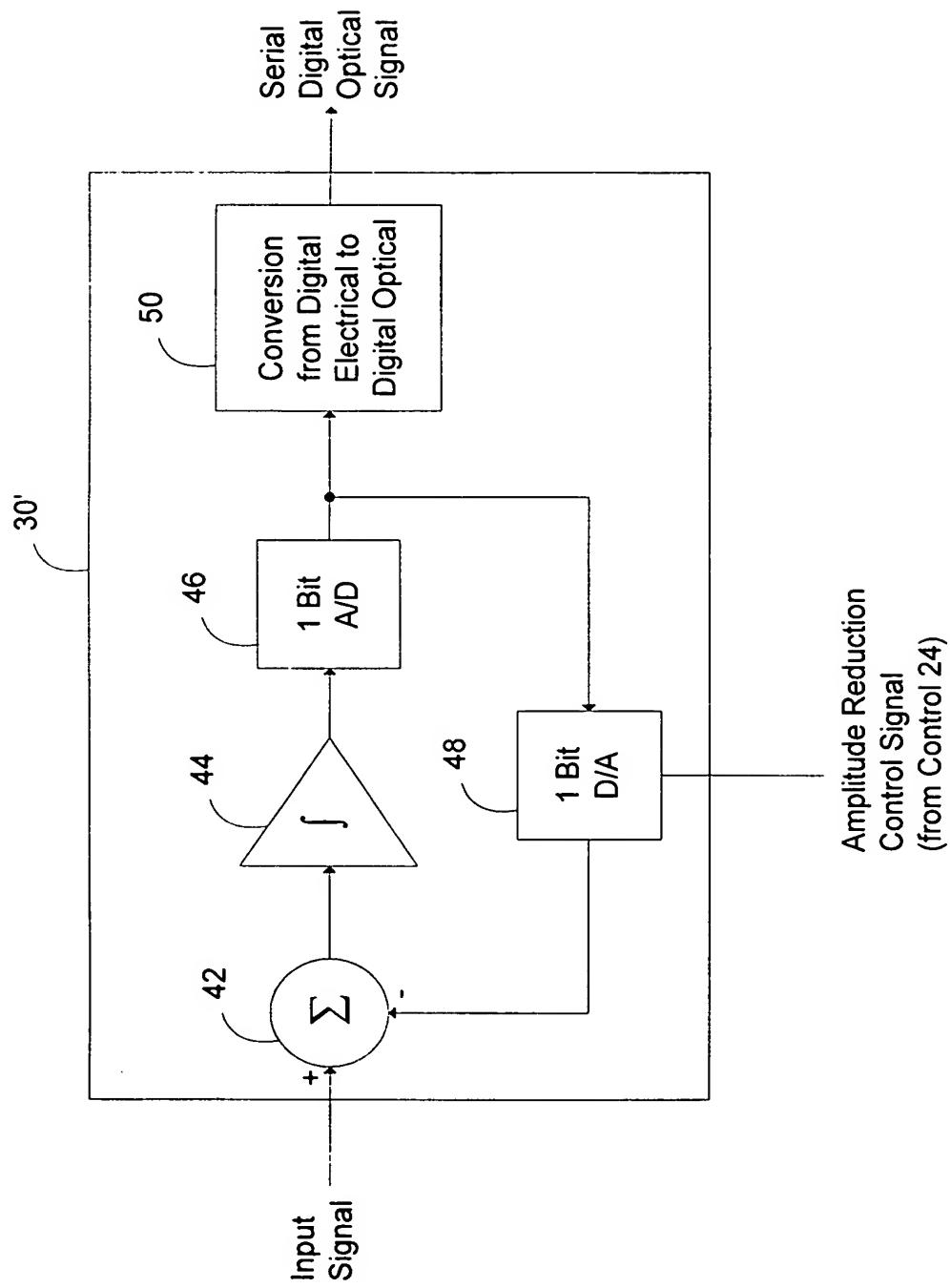


FIG. 3A

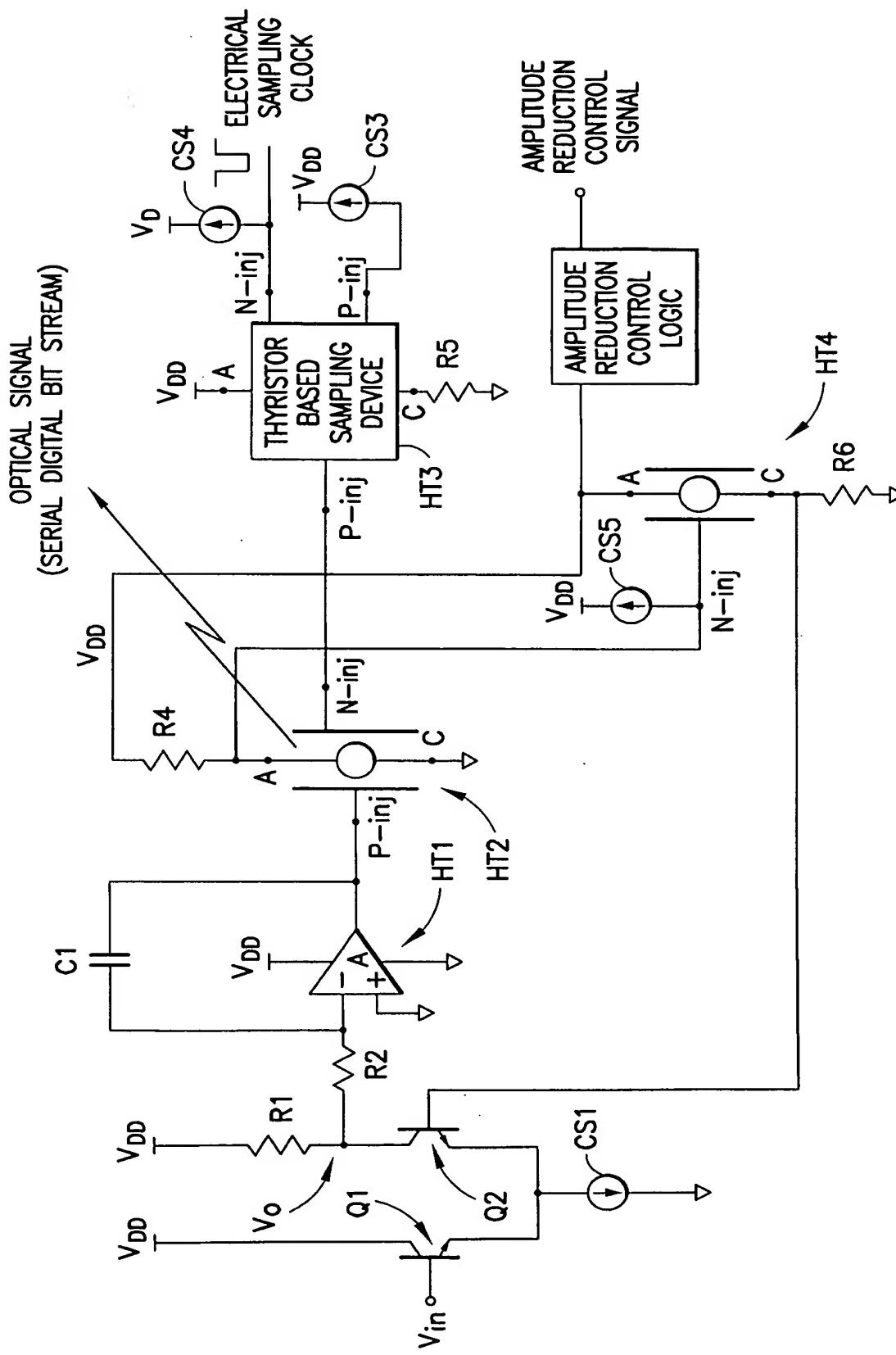


FIG. 3B1

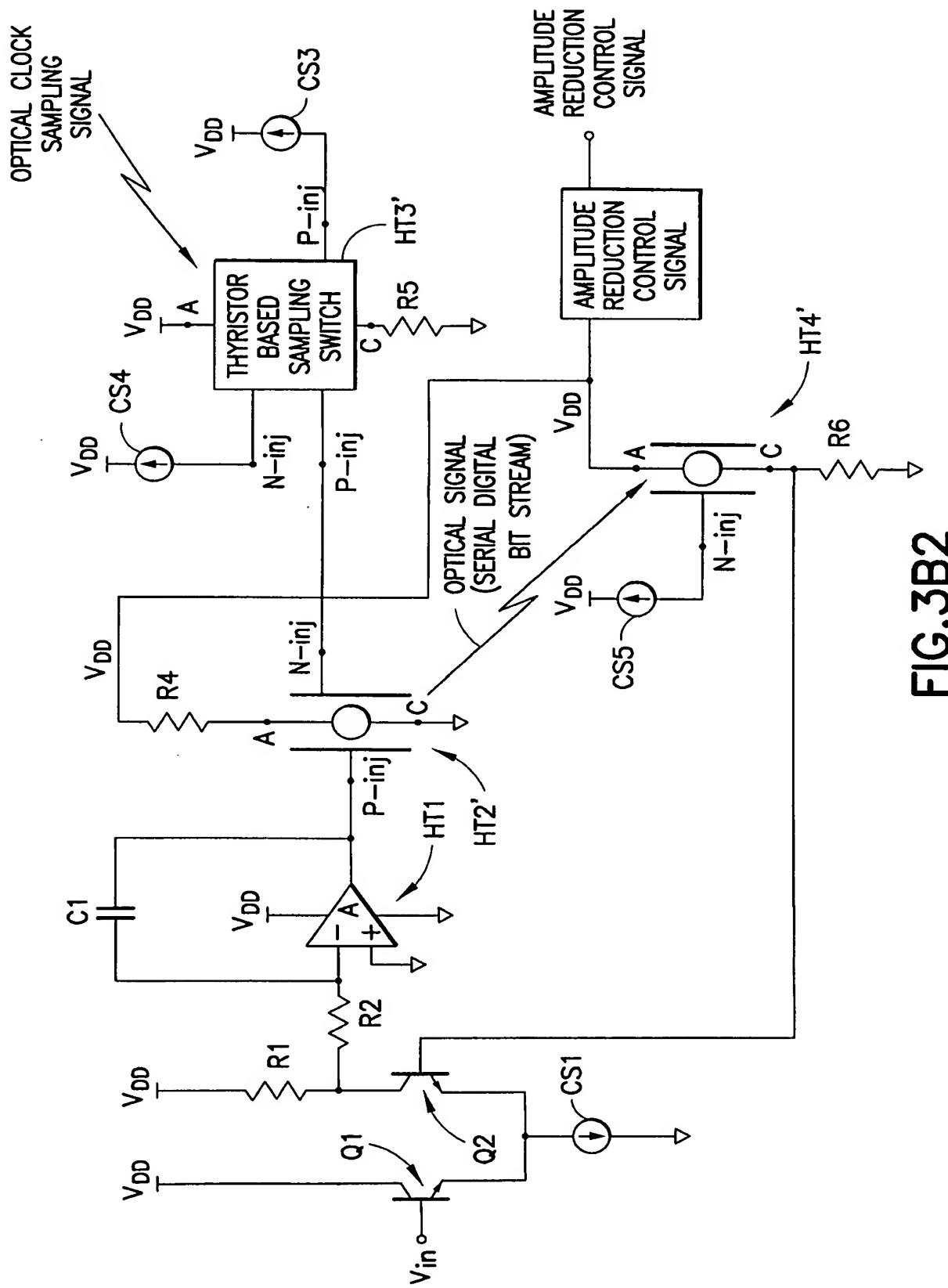


FIG.3B2

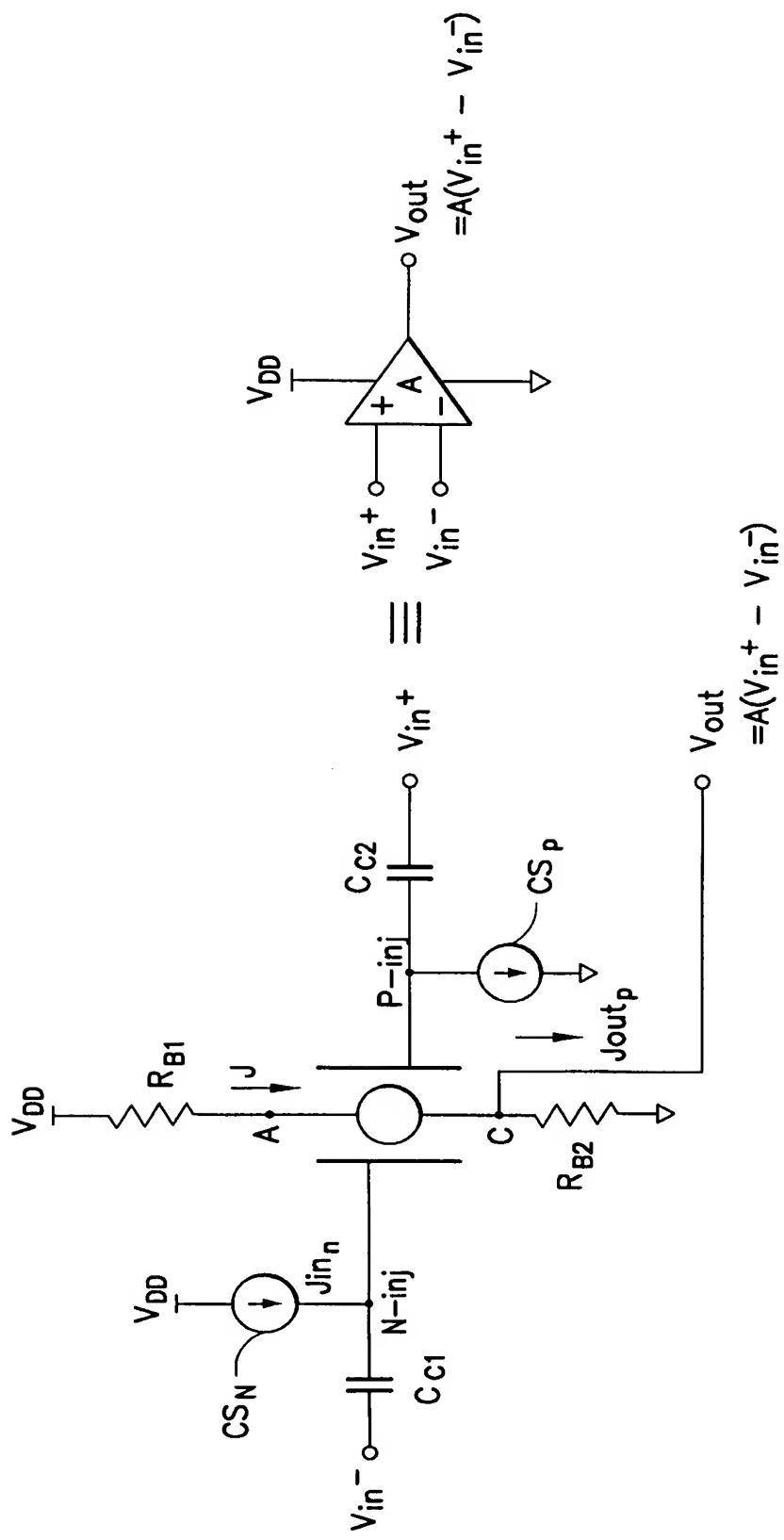


FIG.3C1

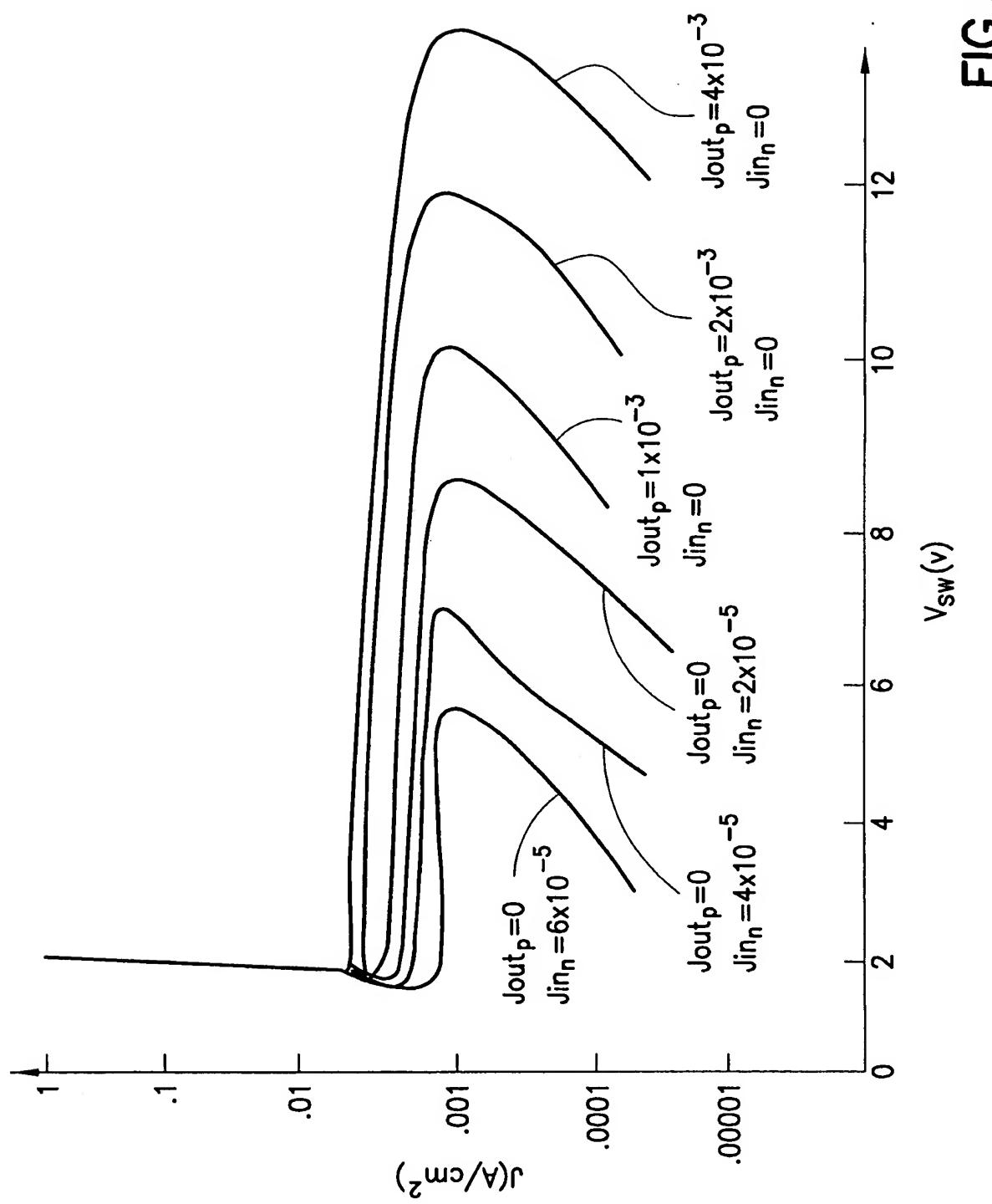


FIG.3C2

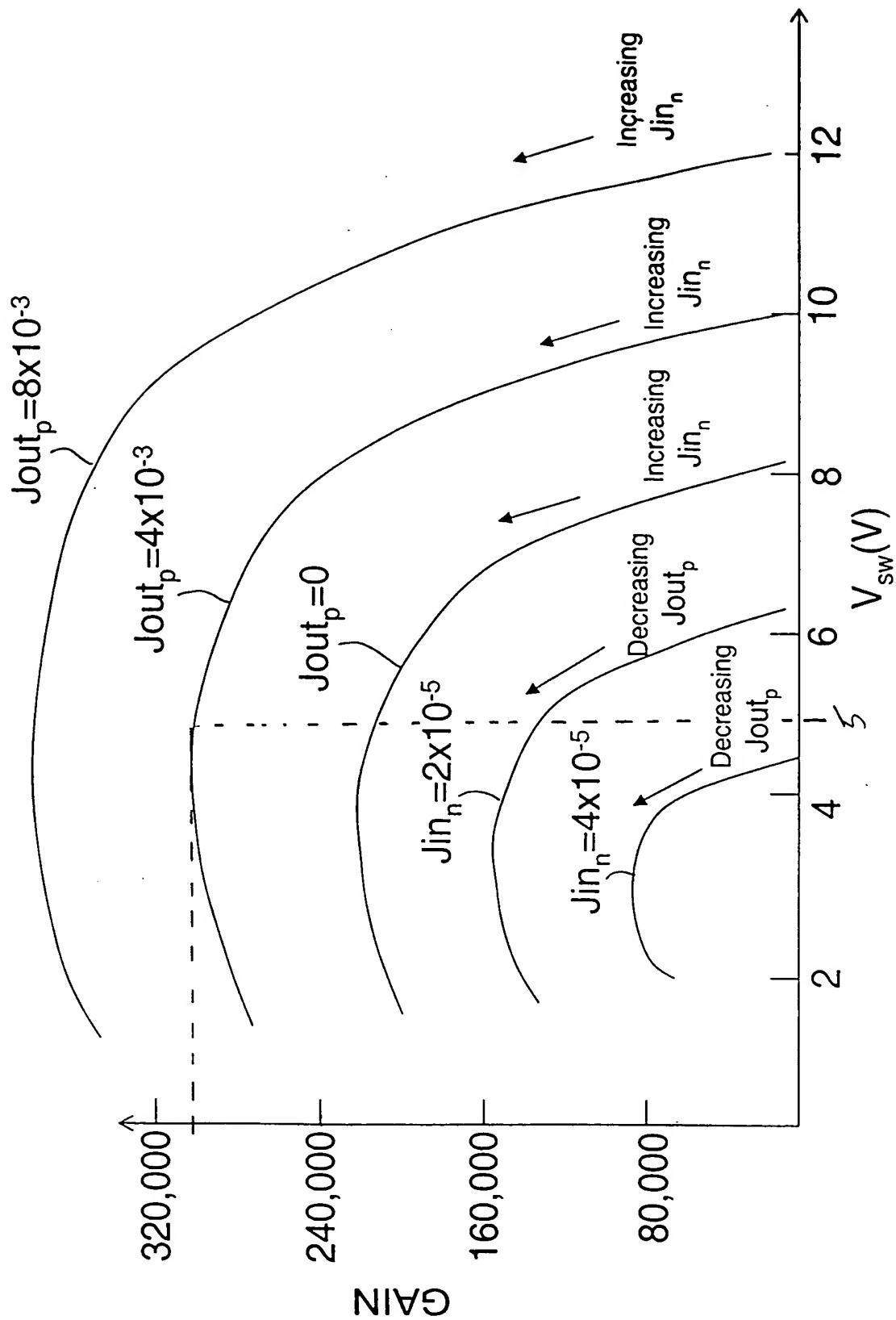


FIG.3C3

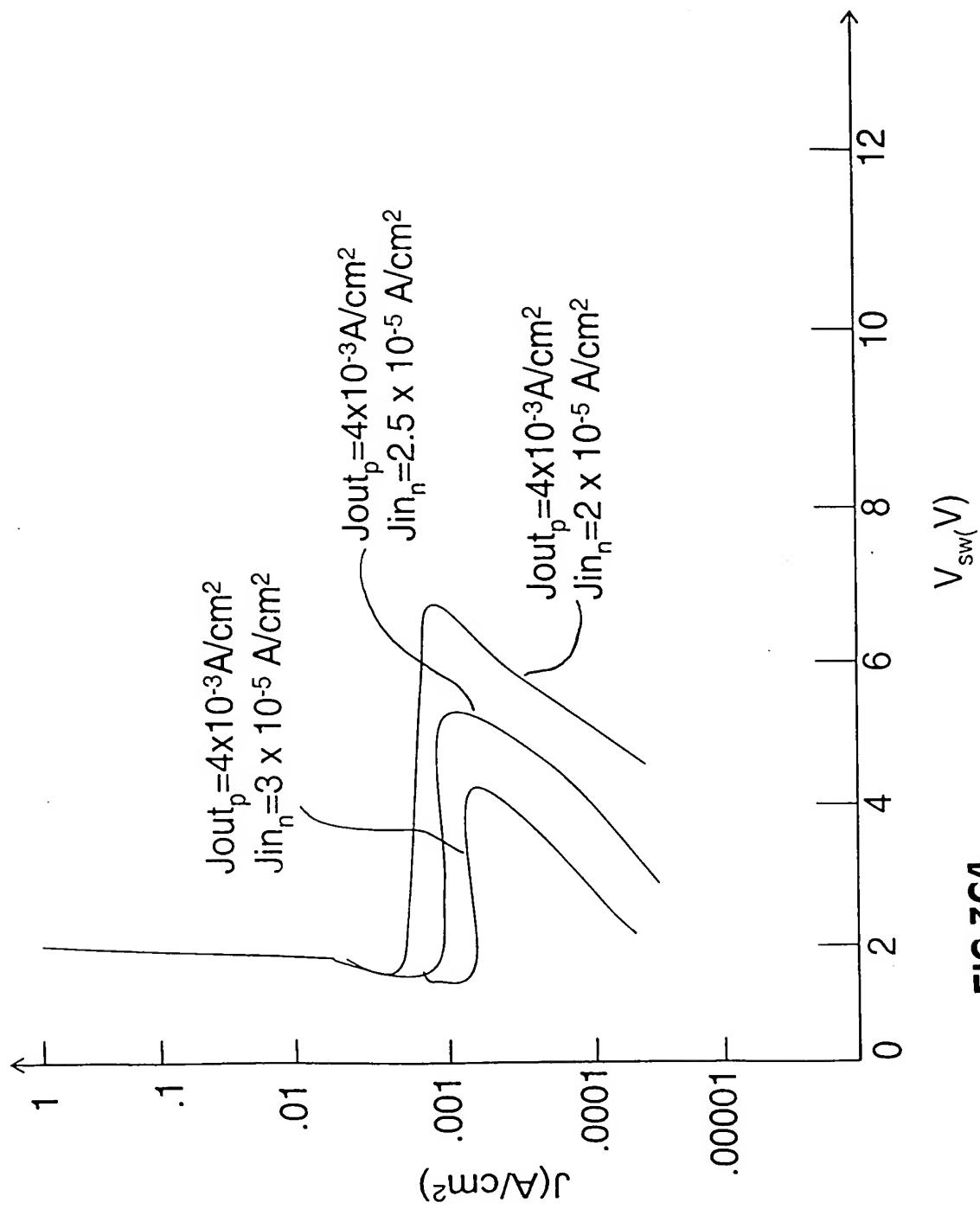


FIG.3C4

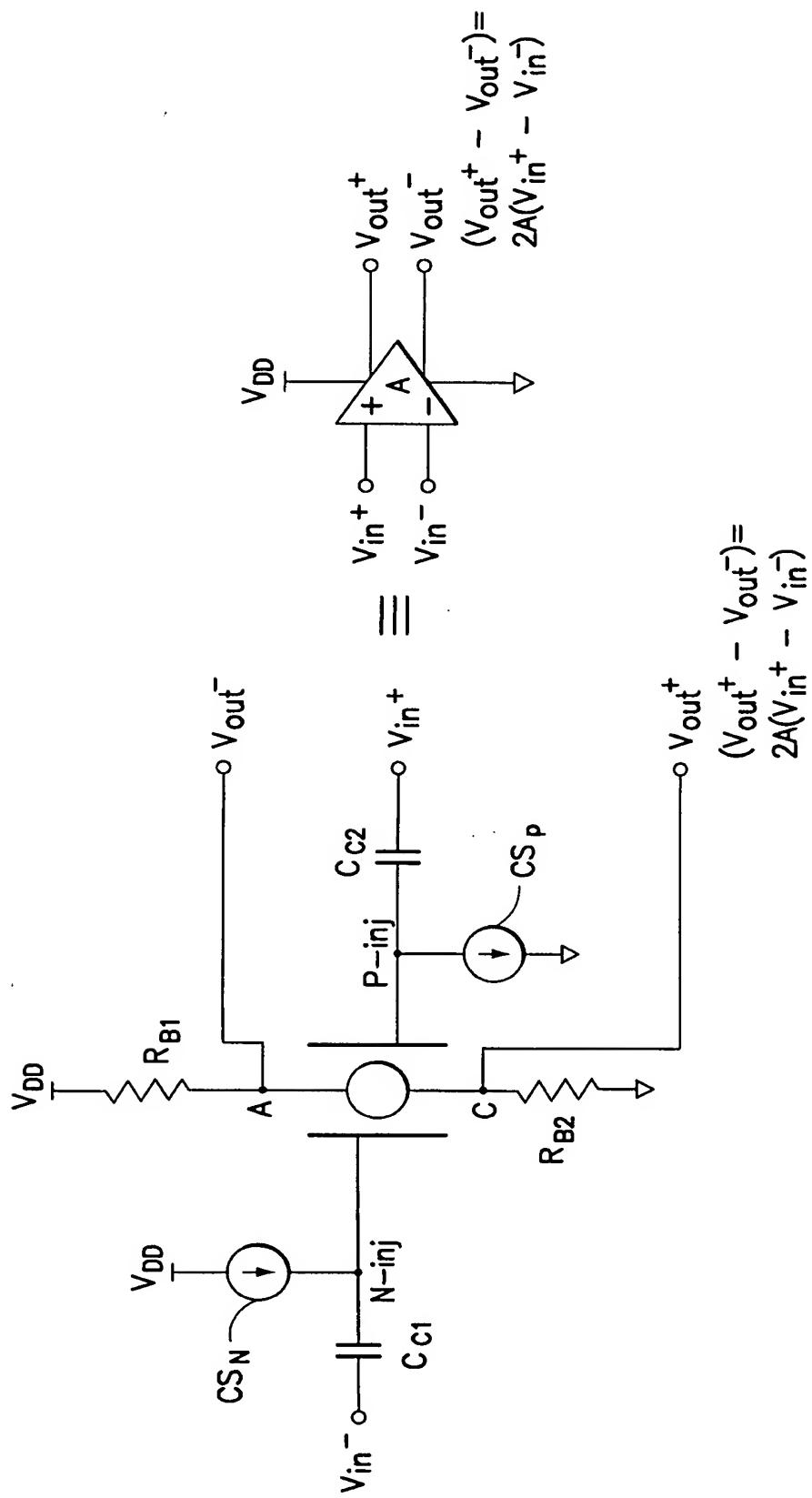
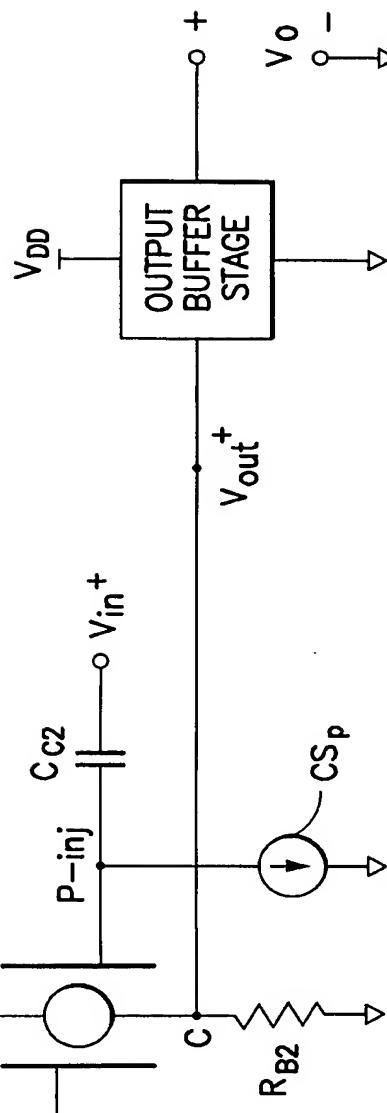
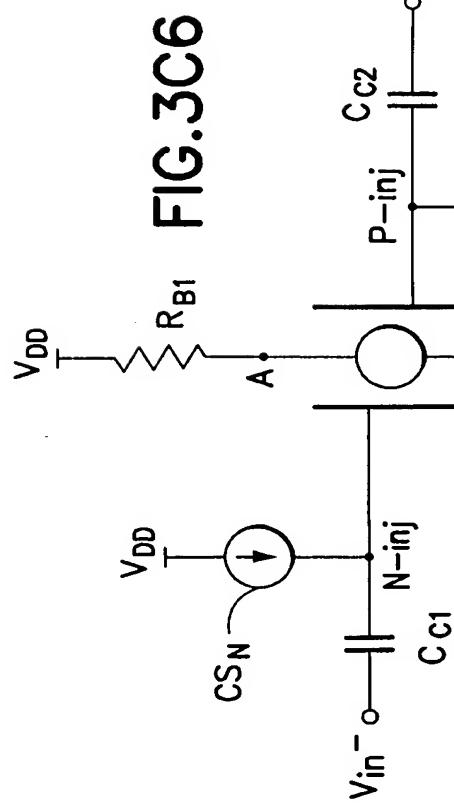
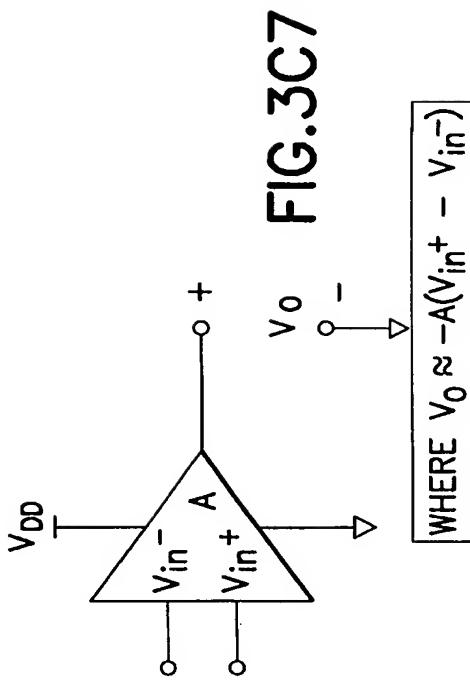


FIG. 3C5



WHERE $V_o \approx -A(V_{in}^+ - V_{in}^-)$



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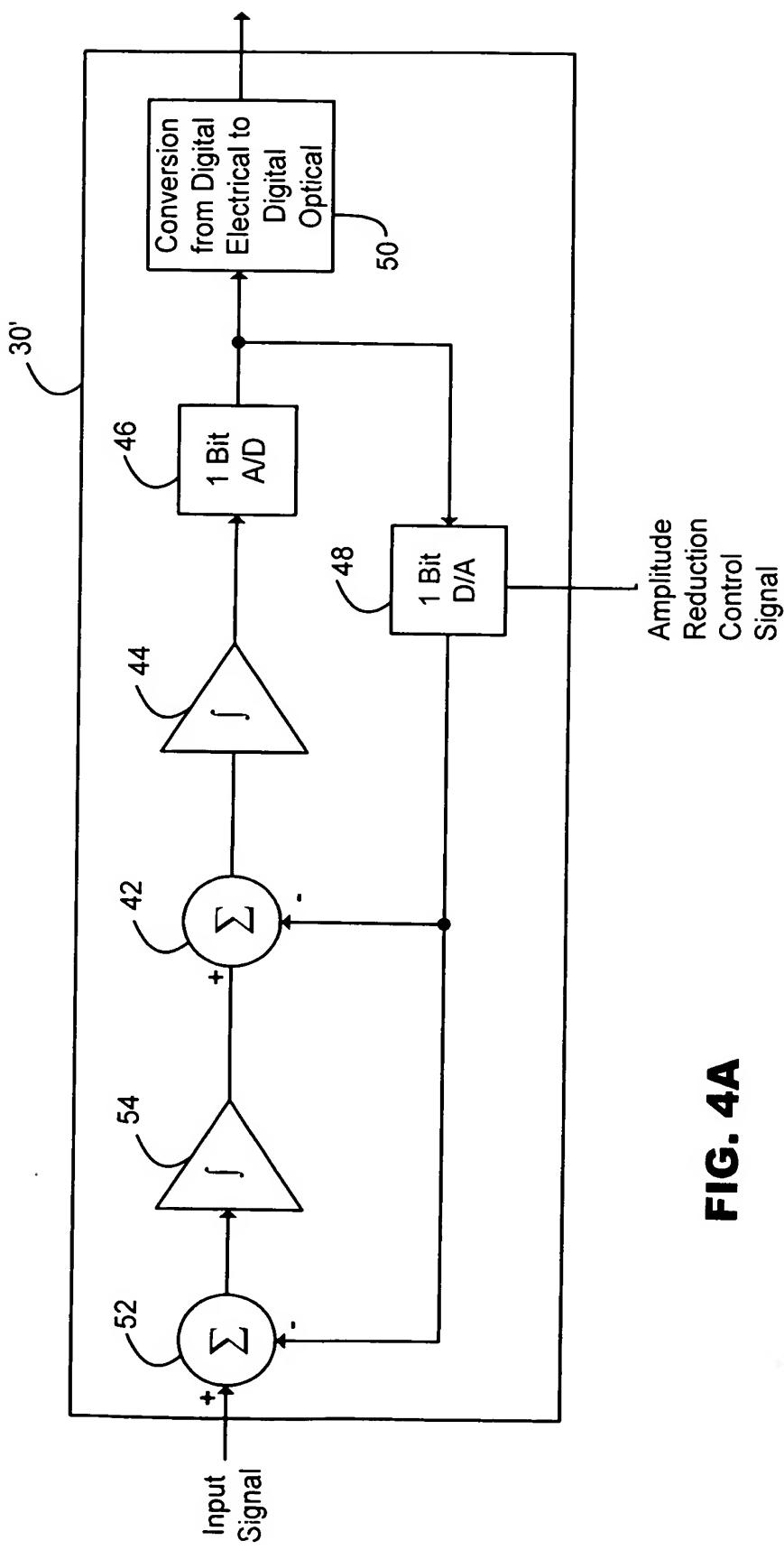


FIG. 4A

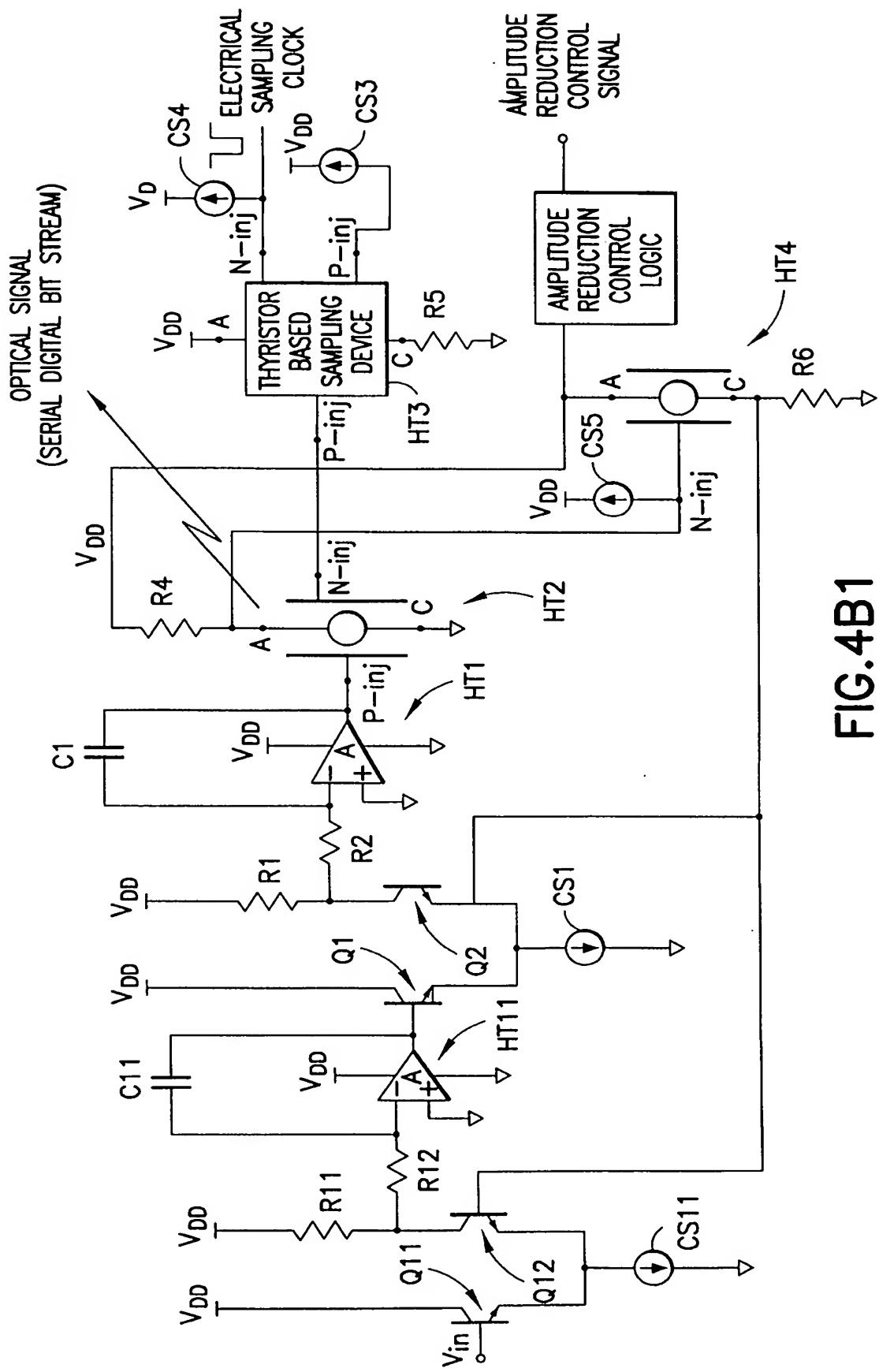


FIG. 4B1

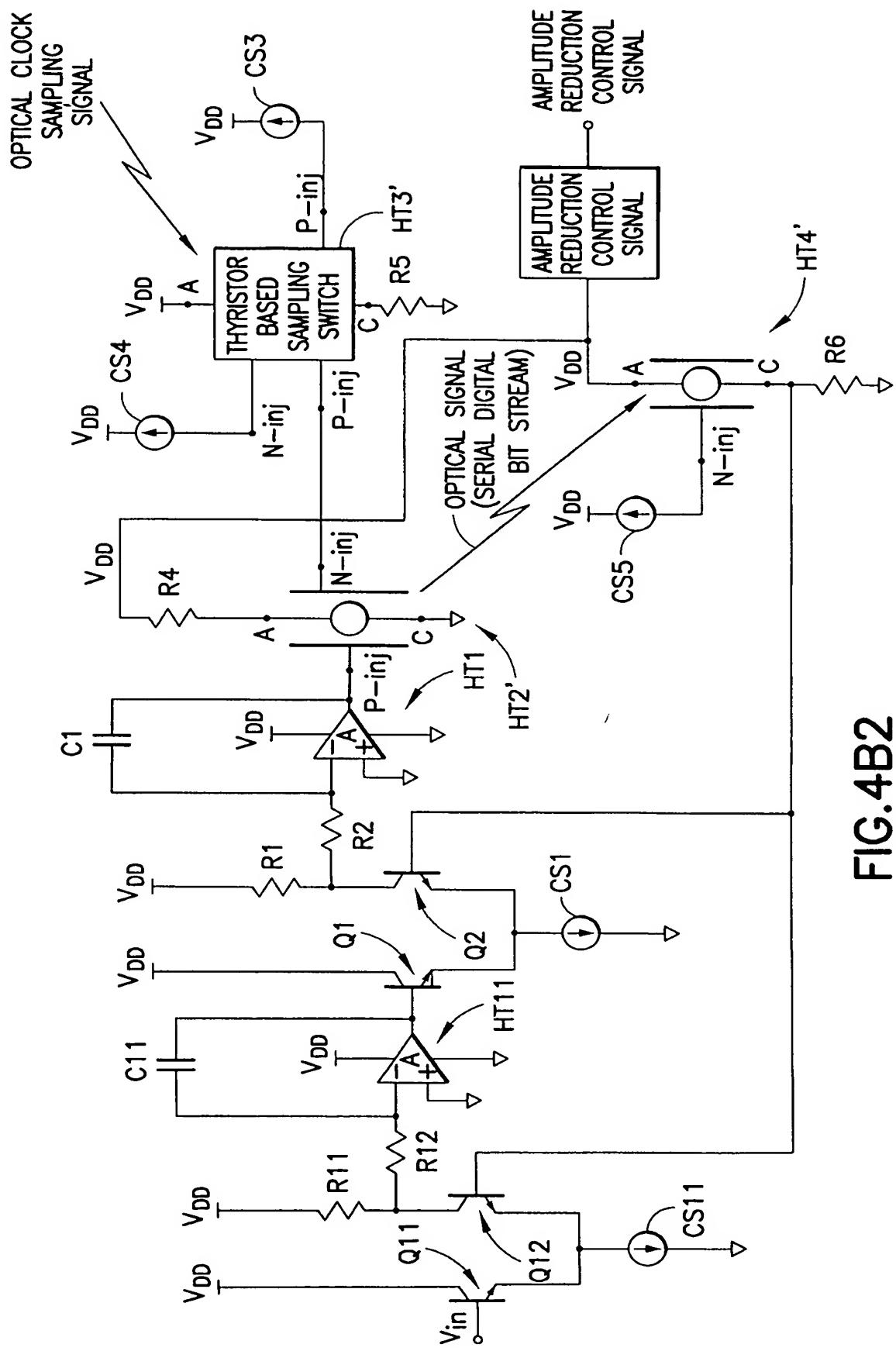


FIG. 4B2

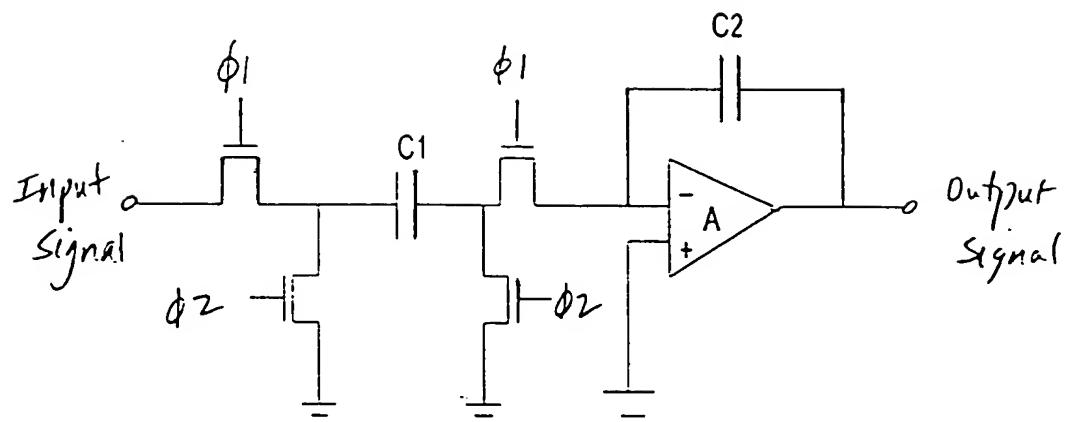


FIG.4B3

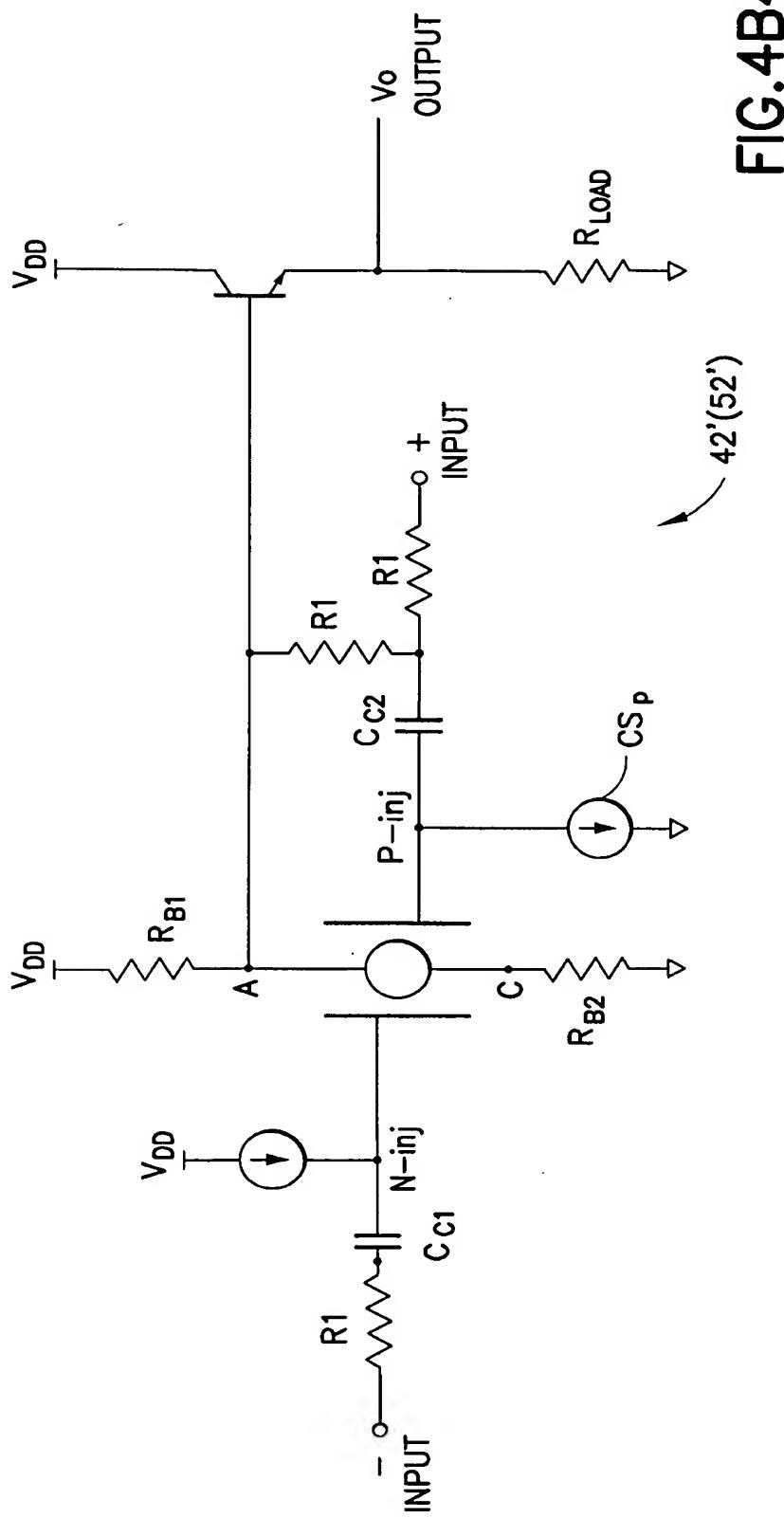


FIG. 4B4

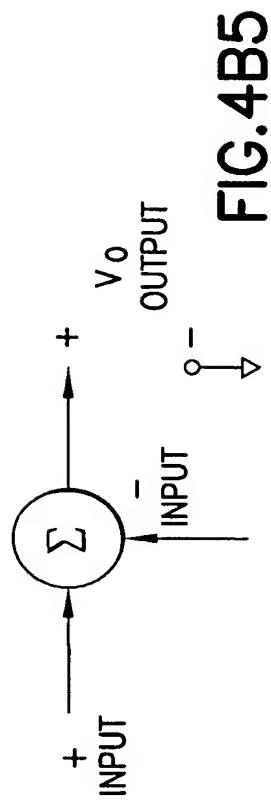


FIG. 4B5

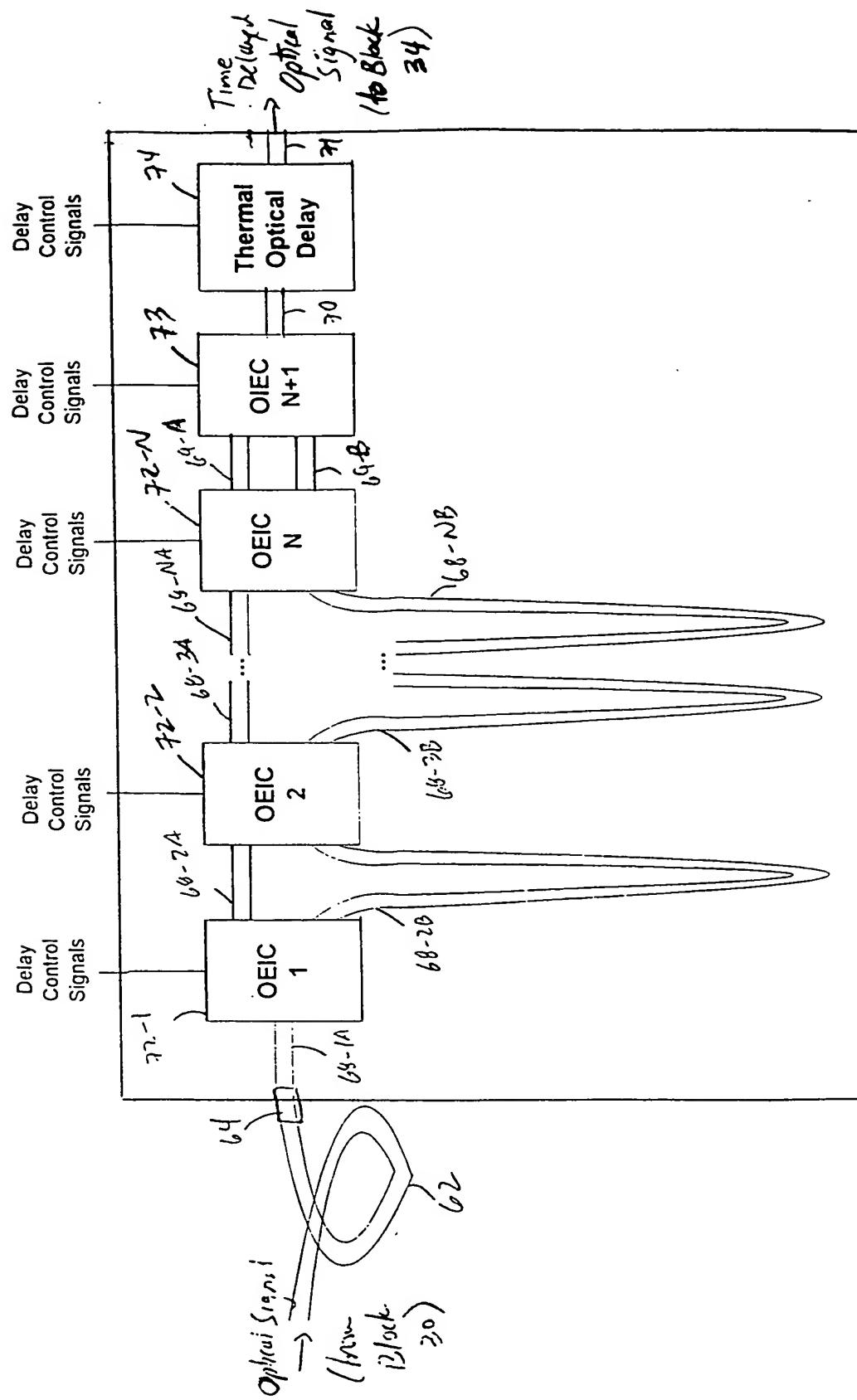


FIG.5A

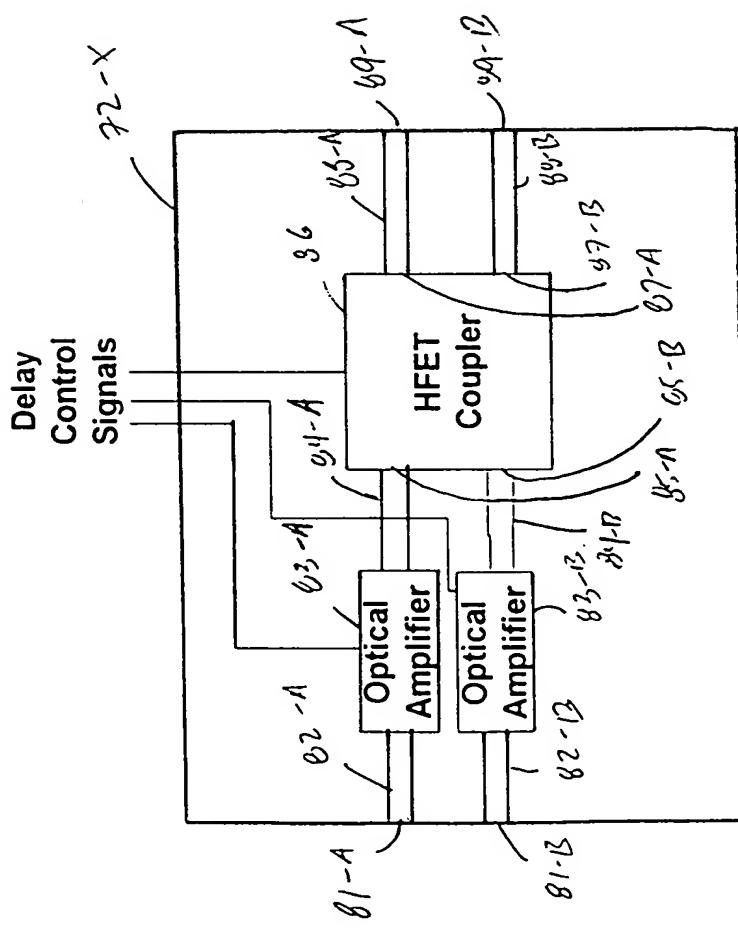
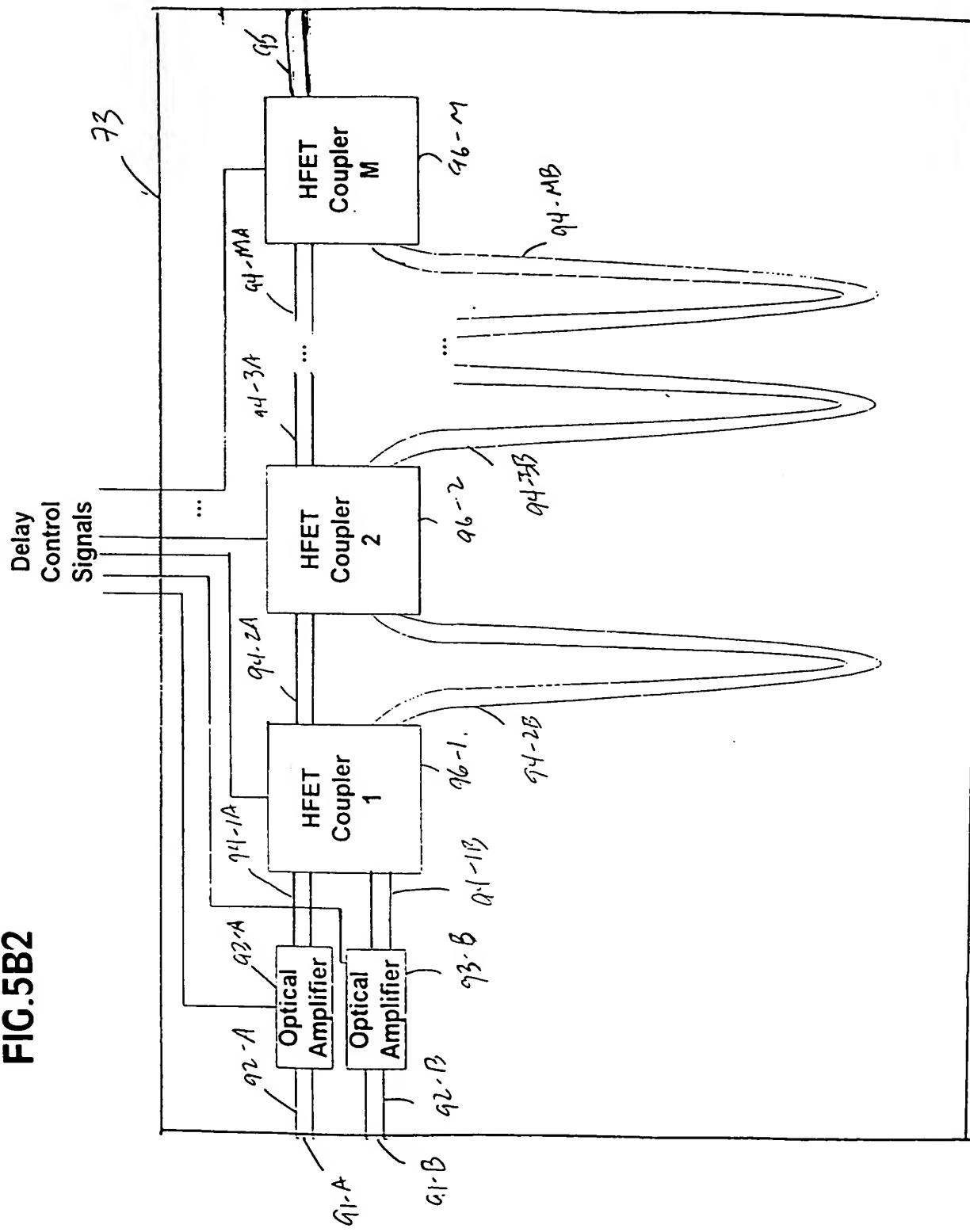


FIG.5B1

FIG.5B2



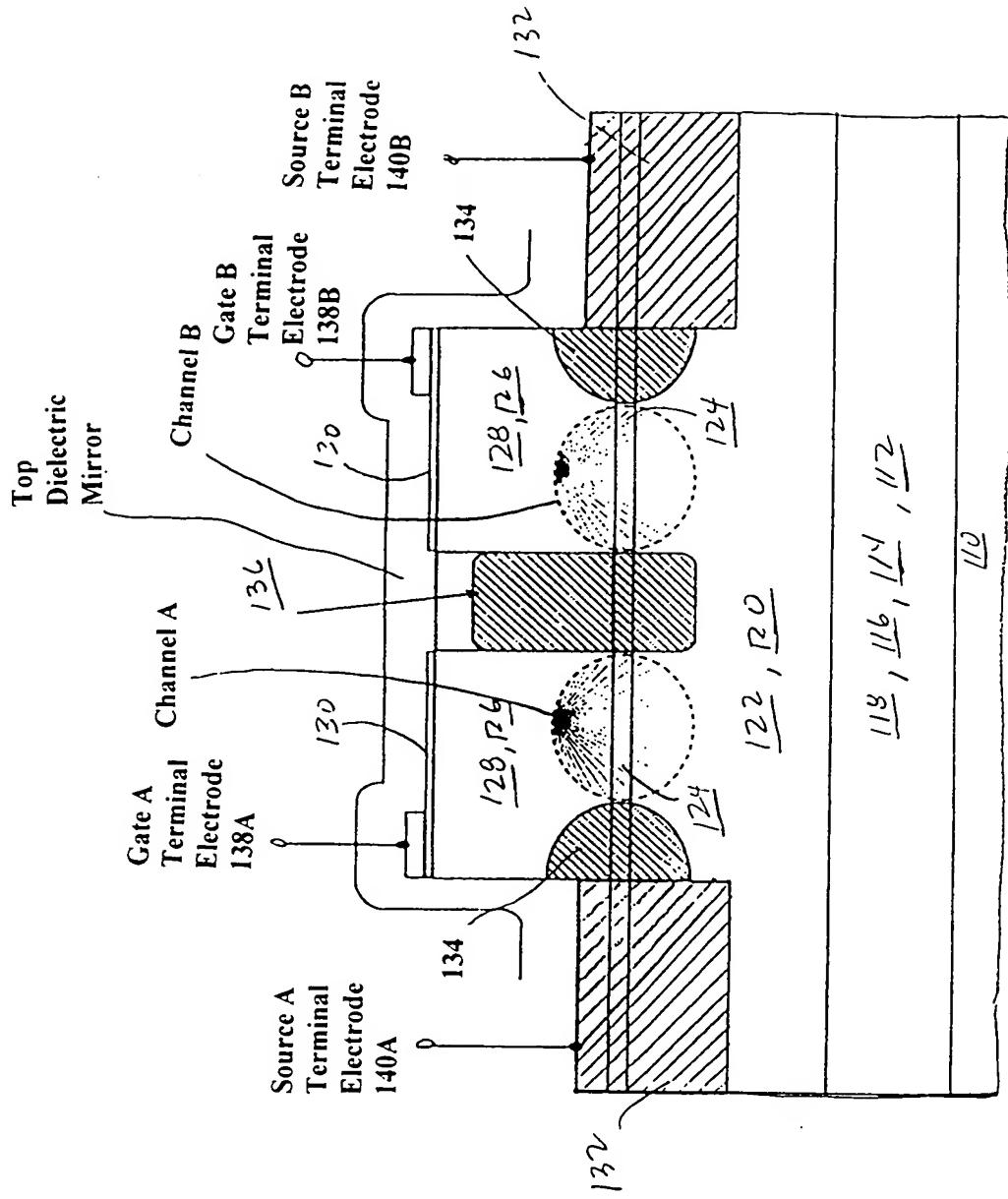


FIG. 5C1

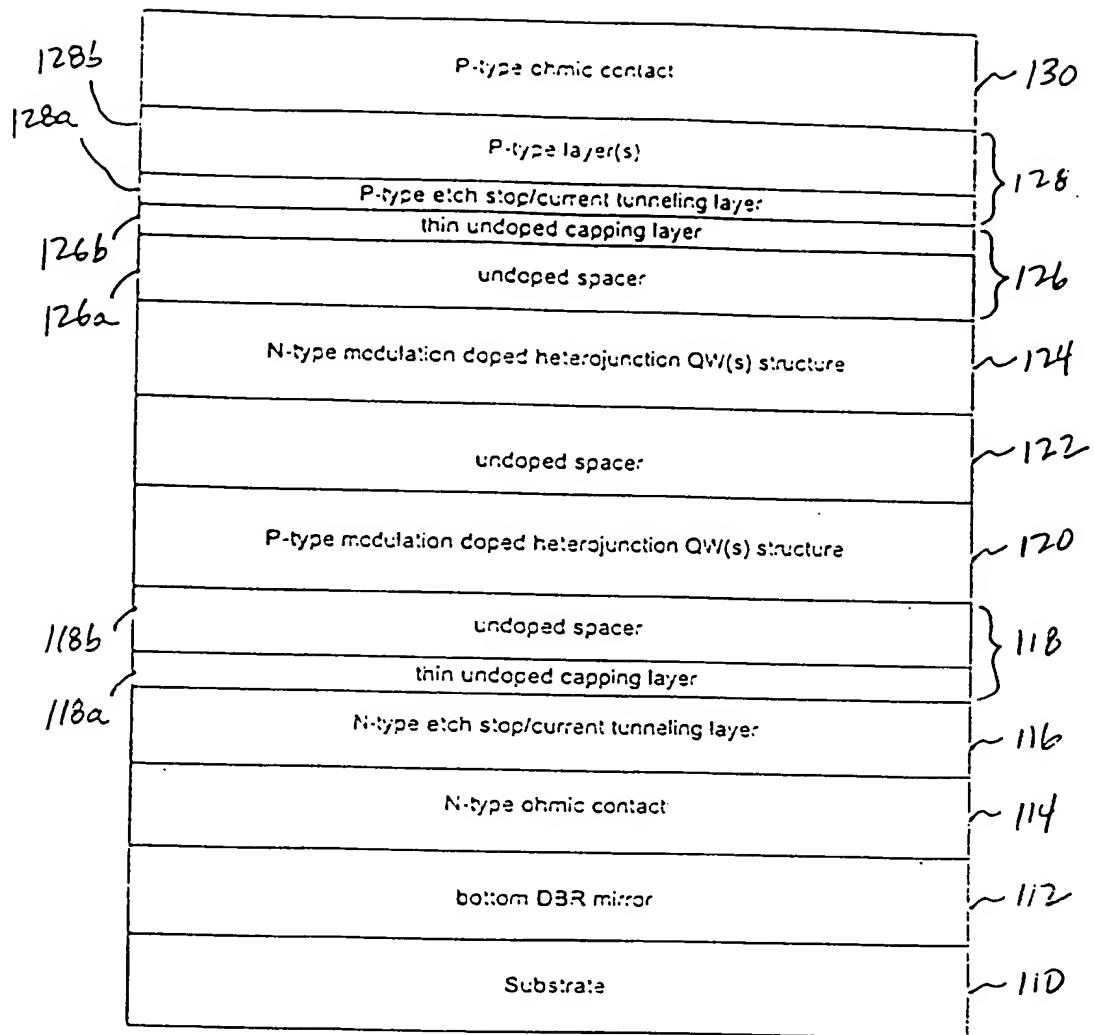


FIG.5C2

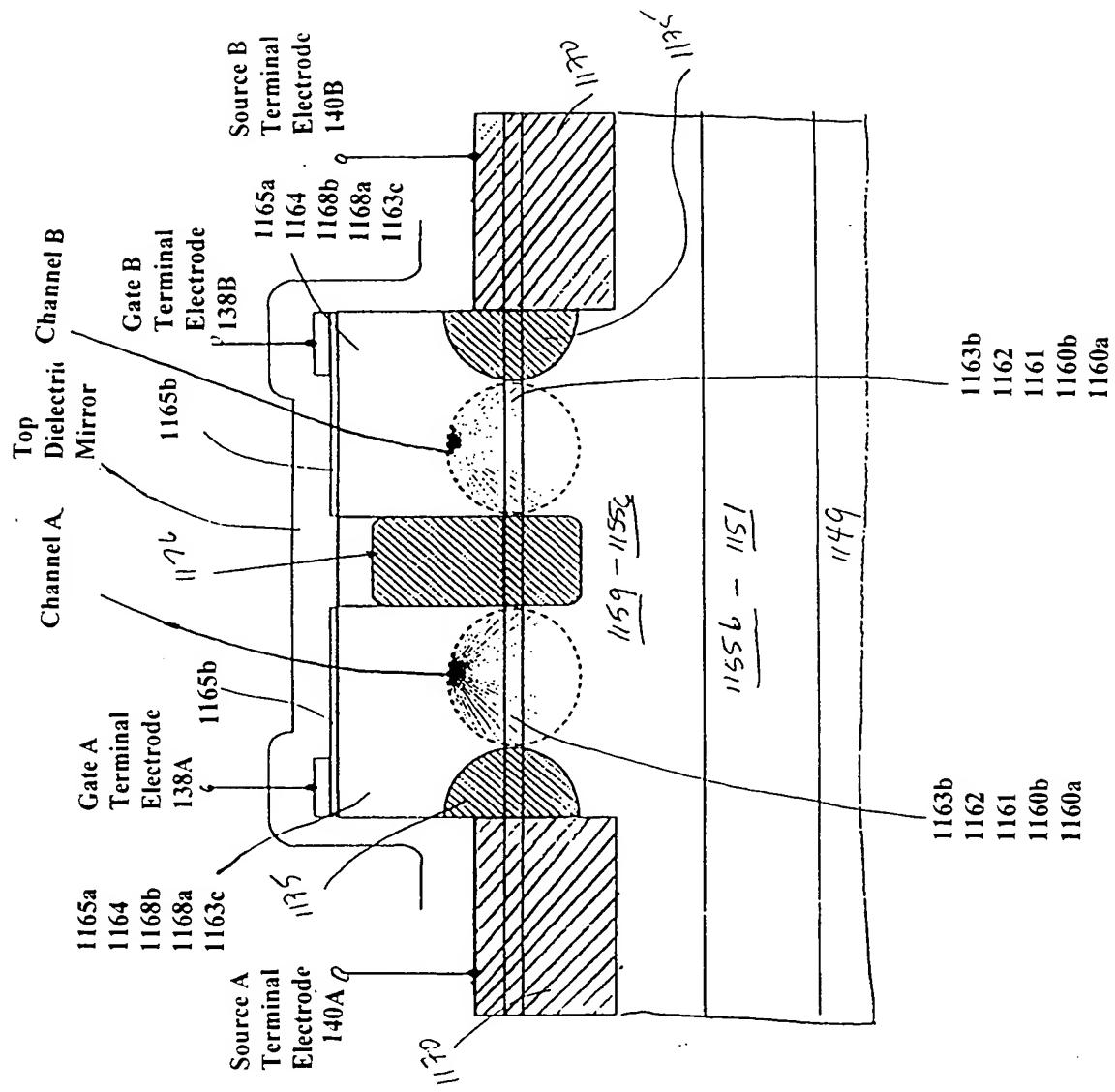


FIG. 5D1

Layer Material	Layer Doping Type	Typical Doping Concentration (atoms/cm ³)	Typical Layer Thickness (Å)	Layer #
InGaAs	p+	1E20	25	1165b
GaAs	p+	1E20	75	1165a
GaAs	p	1.5E17	300	1164
AlAs	p+	3.5E18	>20, <300	1168b
GaAs	und	und	>6, <20	1168a
Al _{0.15} Ga _{0.85} As	und	und	200 - 300	1163c
Al _{0.15} Ga _{0.85} As	n+	3.5E18	80	1163b
GaAs	und	und	20-30	1163a
In _{0.15} Ga _{0.85} AsN	und	und	15	1162
GaAs } x3	und	und	60	1161
GaAs	und	und	100	1160b
Al _{0.15} Ga _{0.85} As	und	und	100 - 250	1160a
GaAs	und	und	5000	1159
GaAs }	und	und	250 - 500	1167
In _{0.15} Ga _{0.85} AsN } x3	und	und	100	1158
GaAs	und	und	60	1157
Al _{0.15} Ga _{0.85} As	und	und	15	1156
Al _{0.15} Ga _{0.85} As	p+	3.5E18	30	1155d
Al _{0.15} Ga _{0.85} As	und	und	80	1155c
GaAs	und	und	200-300	1155b
AlAs	und	und	>6, <20	1166b
AlAs	N+	3.5E18	>30, <200	1166a
GaAs	N+	3.5E18	1000 - 2000	1153
AlAs	und	und	1701	1151
GaAs } x7	und	und	696	1152
AlAs }	und	und	1701	1151
GaAs Substrate		Si		1149

FIG.5D2

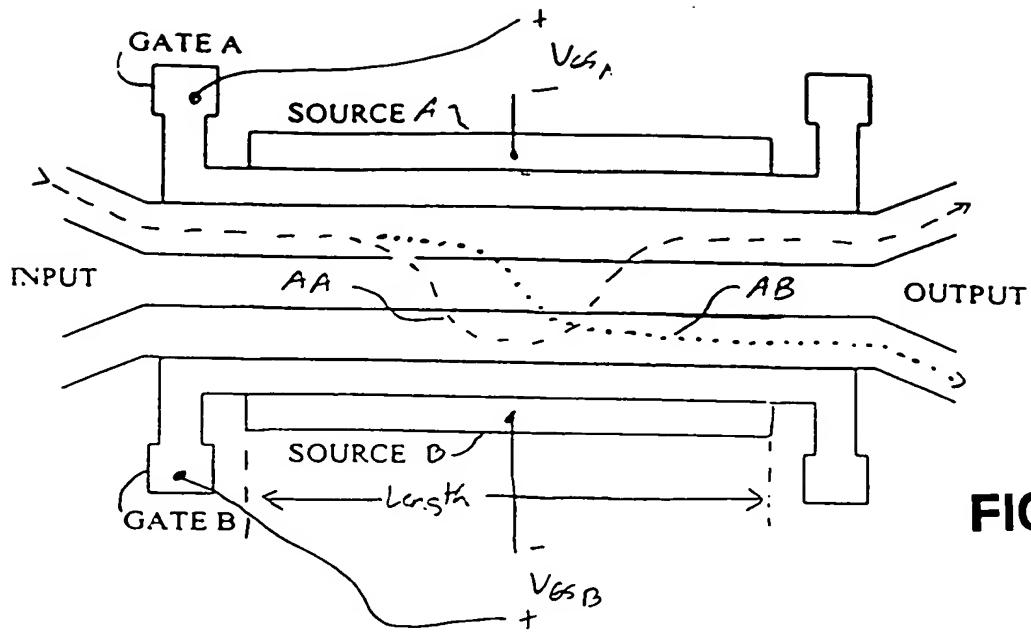


FIG.5E1

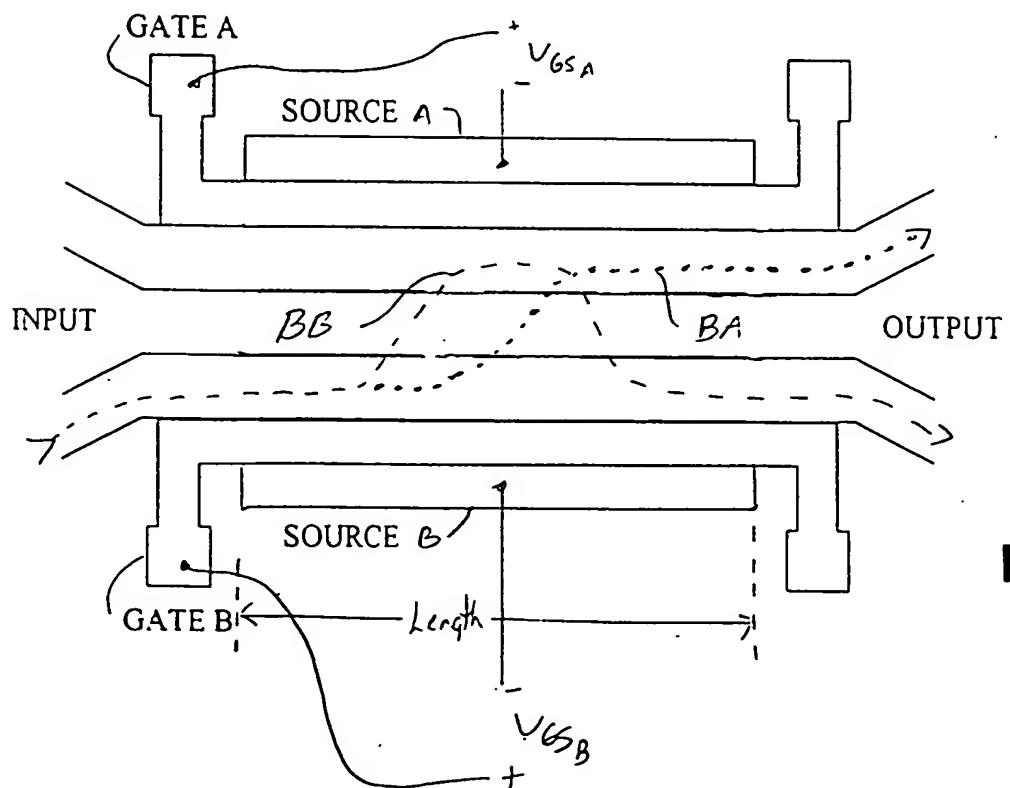


FIG.5E2

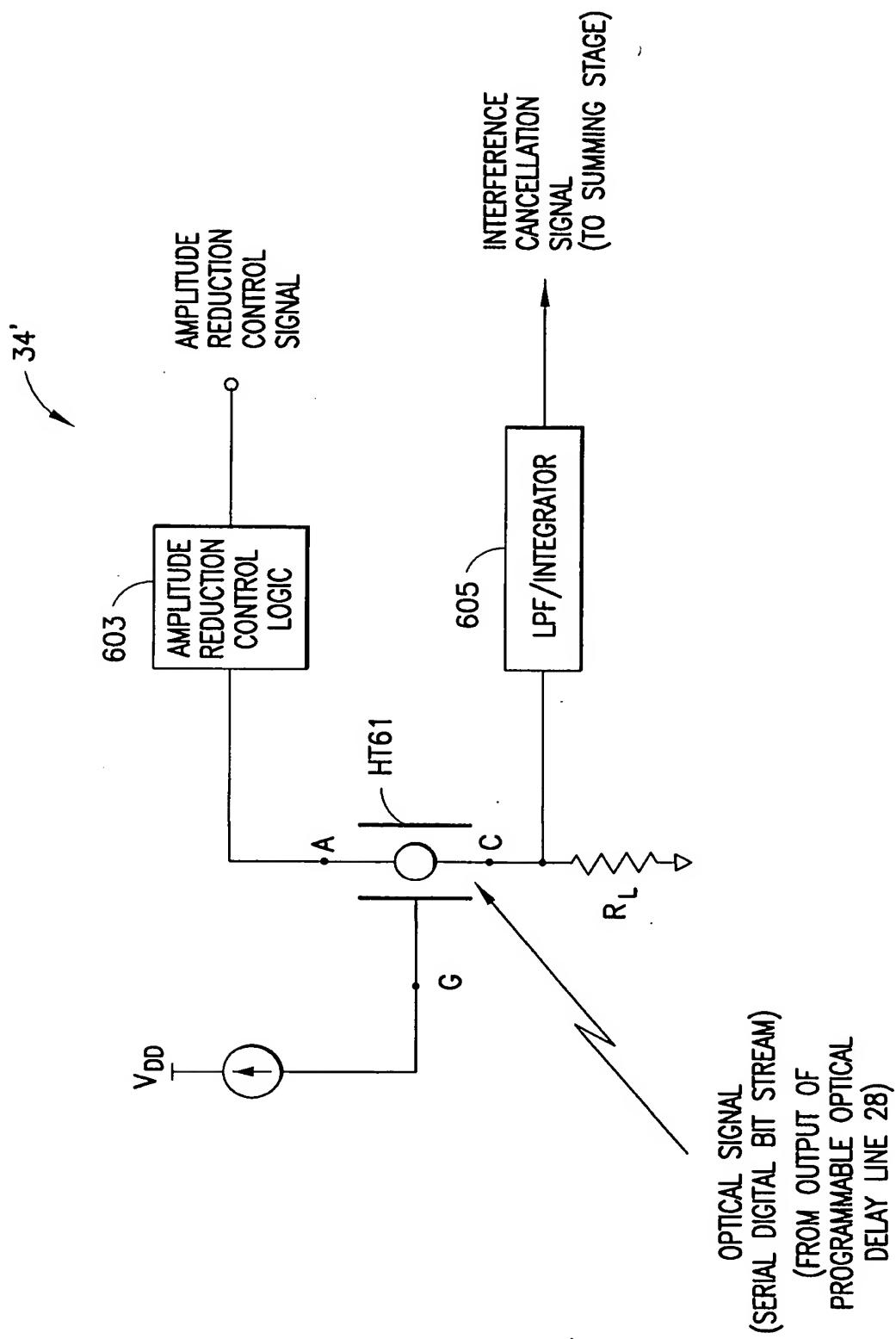


FIG.6

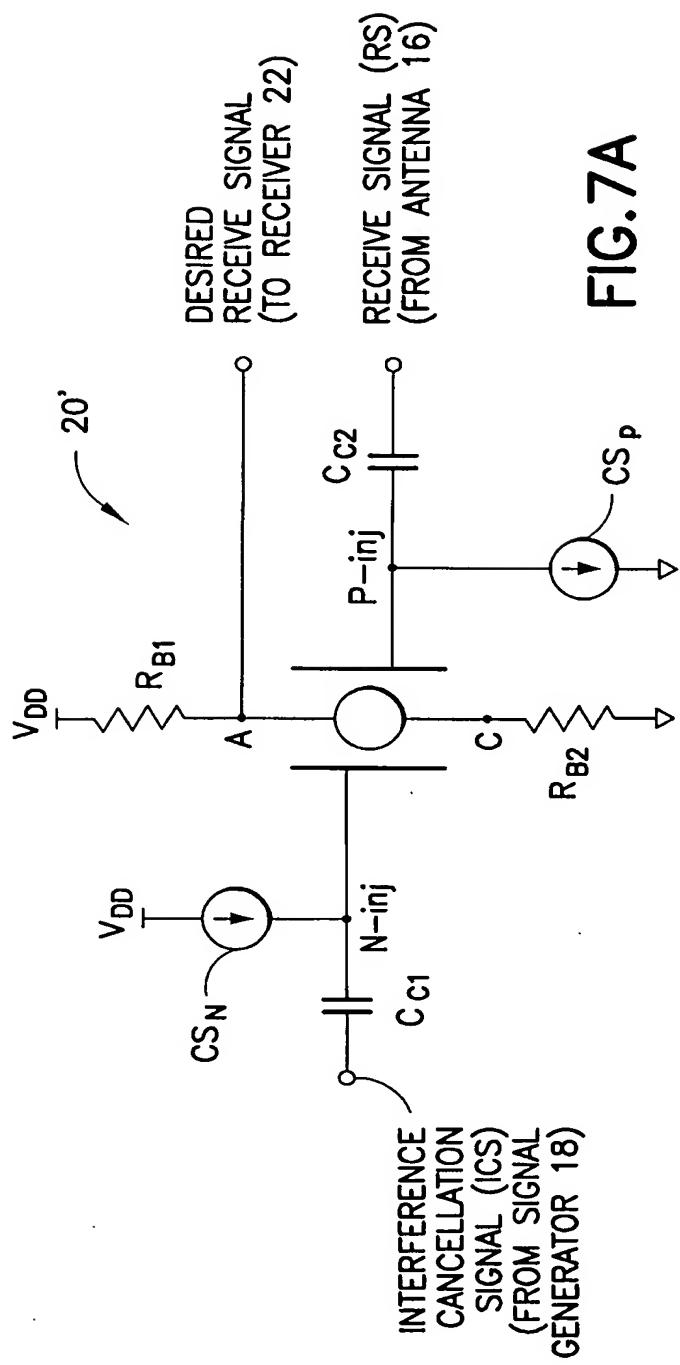


FIG.7A

